AMENDMENTS TO THE CLAIMS

Please **AMEND** claims 2 as follows.

Please **CANCEL** claims 1, 8-13, 20, and 31-41 without prejudice or disclaimer.

A copy of all pending claims and a status of the claims is provided below.

1. (canceled)

2. (currently amended) ~~The method of claim 1,~~ A method, comprising:

forming a pattern of strained material and relaxed material on a substrate;

forming a strained device in the strained material; and

forming a non-strained device in the relaxed material,

wherein the step of forming a pattern of strained material and relaxed material on a substrate further comprises:

forming a recess in the substrate, the recess having sidewalls;

forming a buffer layer in the recess which has a lattice constant/structure mismatch with the substrate;

forming a relaxed layer on the buffer layer;

forming the strained material on the relaxed layer and the relaxed material on the substrate, wherein the relaxed layer has a lattice constant/structure mismatch with the strained material.

3. (original) The method of claim 2, further comprising forming an insulating layer on the sidewalls before forming the buffer layer.

4. (original) The method of claim 2 wherein the relaxed layer and the buffer layer are each selected from the group consisting of silicon carbon (SiC), silicon germanium (SiGe), $Al_{X1}Ga_{X2}In_{X3}As_{Y1}P_{Y2}N_{Y3}Sb_{Y4}$, where X1, X2, X3, Y1, Y2, Y3, and Y4 represent relative proportions, each greater than or equal to zero and X1+X2+X3+Y1+Y2+Y3+Y4=1 (1 being the total relative mole quantity), and $Zn_{A1}Cd_{A2}Se_{B1}Te_{B2}$, where A1, A2, B1, and B2 are relative proportions each greater than or equal to zero and A1+A2+B1+B2=1 (1 being a total mole quantity).

5. (original) The method of claim 2, wherein the strained material and the relaxed material are each selected from one of the group consisting of silicon (Si), silicon carbon (SiC), silicon germanium (SiGe), $Al_{X1}Ga_{X2}In_{X3}As_{Y1}P_{Y2}N_{Y3}Sb_{Y4}$, where X1, X2, X3, Y1, Y2, Y3, and Y4 represent relative proportions, each greater than or equal to zero and X1+X2+X3+Y1+Y2+Y3+Y4=1, and $Zn_{A1}Cd_{A2}Se_{B1}Te_{B2}$, where A1, A2, B1, and B2 are relative proportions each greater than or equal to zero and A1+A2+B1+B2=1.

6. (original) The method of claim 2, wherein the step of forming the buffer layer further comprises:

epitaxially growing multiple layers of a material forming the buffer layer such that the material forming the buffer layer has a base concentration proximate the substrate and an increased benchmark concentration proximate the relaxed layer.

7. (original) The method of claim 6, wherein the step of forming the relaxed layer further comprises:

epitaxially growing multiple layers of a material forming the relaxed layer such that the material forming the relaxed layer has a second base concentration proximate the buffer layer that approximately equals the bench-mark concentration of the buffer layer material.

8. – 41. (canceled)